



DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
50V	1.6Ω @ V _{GS} = 10V	360mA
	2.5Ω @ V _{GS} = 4.5V	250mA

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD protected to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

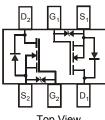
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208⁽²⁾
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Top View



Top View Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN53D0LDW-7	SOT363	3000/Tape & Reel
DMN53D0LDW-13	SOT363	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

		[
Γ	Μ	M5		YM				
	N	К	9	MN	1			
Т	Т	Т	Т					

MM5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Date Code Key												
Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D	l	Ξ	F		G		Н
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	ID	360	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

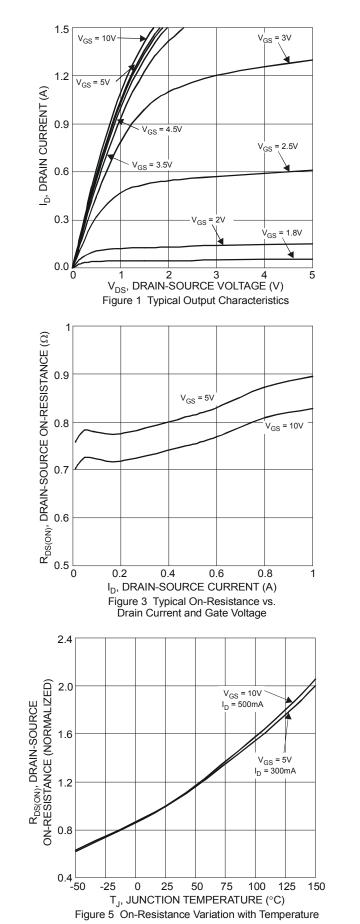
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	R ₀ JA	411	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

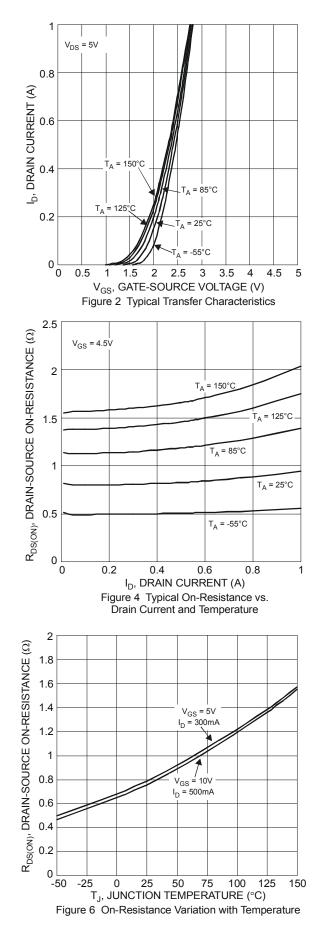
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	50		_	V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μA	V _{DS} = 50V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}		_	10	μA	V_{GS} = ±20V, V_{DS} = 0V	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.8		1.5	V	V_{DS} = V_{GS} , I_D = 250 μ A	
				1.6		V _{GS} = 10V, I _D = 500mA	
Static Drain-Source On-Resistance	R _{DS (ON)}			2.5	Ω	V _{GS} = 4.5V, I _D = 200mA	
		_	—	4.5		V_{GS} = 2.5V, I_{D} = 100mA	
Source-Drain Diode Forward Voltage	V _{SD}			1.4	V	V_{GS} = 0V, I_{S} = 500mA	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		46	—	pF		
Output Capacitance	C _{oss}	_	5.3	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	4.0	—	pF	1 - 1.0Wi12	
Total Gate Charge	Qg	_	0.6	_	nC		
Gate-Source Charge	Q _{gs}	_	0.2	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA	
Gate-Drain Charge	Q _{gd}	_	0.1	_	nC		
Turn-On Delay Time	t _{D(on)}		2.7	_	ns		
Turn-On Rise Time	tr		2.5	_	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA	
Turn-Off Delay Time	t _{D(off)}		19	_	ns		
Turn-Off Fall Time	t _f	_	11	_	ns		

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:

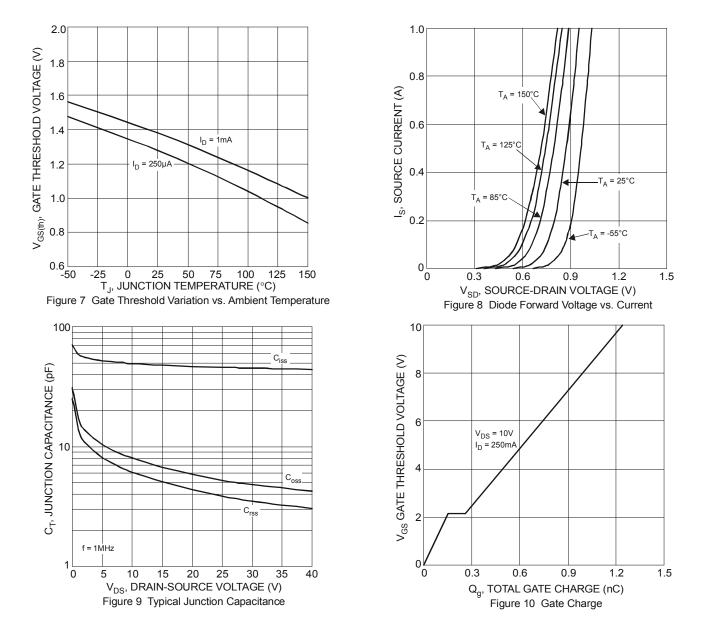






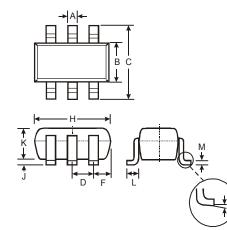
DMN53D0LDW





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

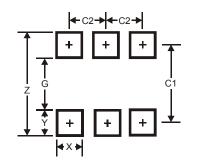


	SOT363					
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D		0.65 Ty	p			
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
κ	0.90	1.00	1.00			
L	0.25	0.40	0.30			
Μ	0.10	0.22	0.11			
α	0°	8°	-			
All	All Dimensions in mm					



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

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